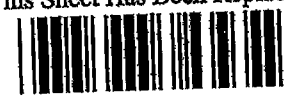
This Sheet Has Been Replaced



ABSTRACT OF THE DISCLOSURE

The conventional fabrication processes of SOI substrate employed wet etching for removing a porous single-crystal Si region, but wet etching involved difficulties in management of concentration for fabricating SOI substrates in high volume, which caused reduction in productivity.

Therefore, provided is a fabrication process of SOI substrate comprises a step of forming a non-porous single-crystal Si region on a surface of a porous single-crystal Si region of a single-crystal Si substrate having at least the porous single-crystal Si region, a step of bonding a support substrate through an insulating region to a surface of the non-porous single-crystal Si region, and a step of removing the porous single-crystal Si region, wherein the step of removing the porous single-crystal Si region comprises a step of performing dry etching in which an etch rate of the porous single-crystal Si region is greater than that of the non-porous single-crystal Si region.